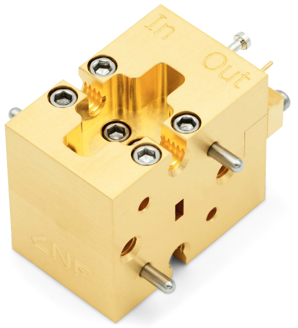
Date
2024-09-24

Datasheet

LNF-LNR65_115WD_SV

65-115 GHz Low Noise Amplifier



Product Features	
RF Bandwidth	65-115 GHz
Noise Temperature	310 K
Noise Figure	3.16 dB
Gain	28 dB
DC power (typical)	V = 5 V, I = 50 mA
RF Connector	WR10, UG-387/U
DC Connectors	2-pin Turret Connector
Single 5V supply only	

Absolute maximum ratings

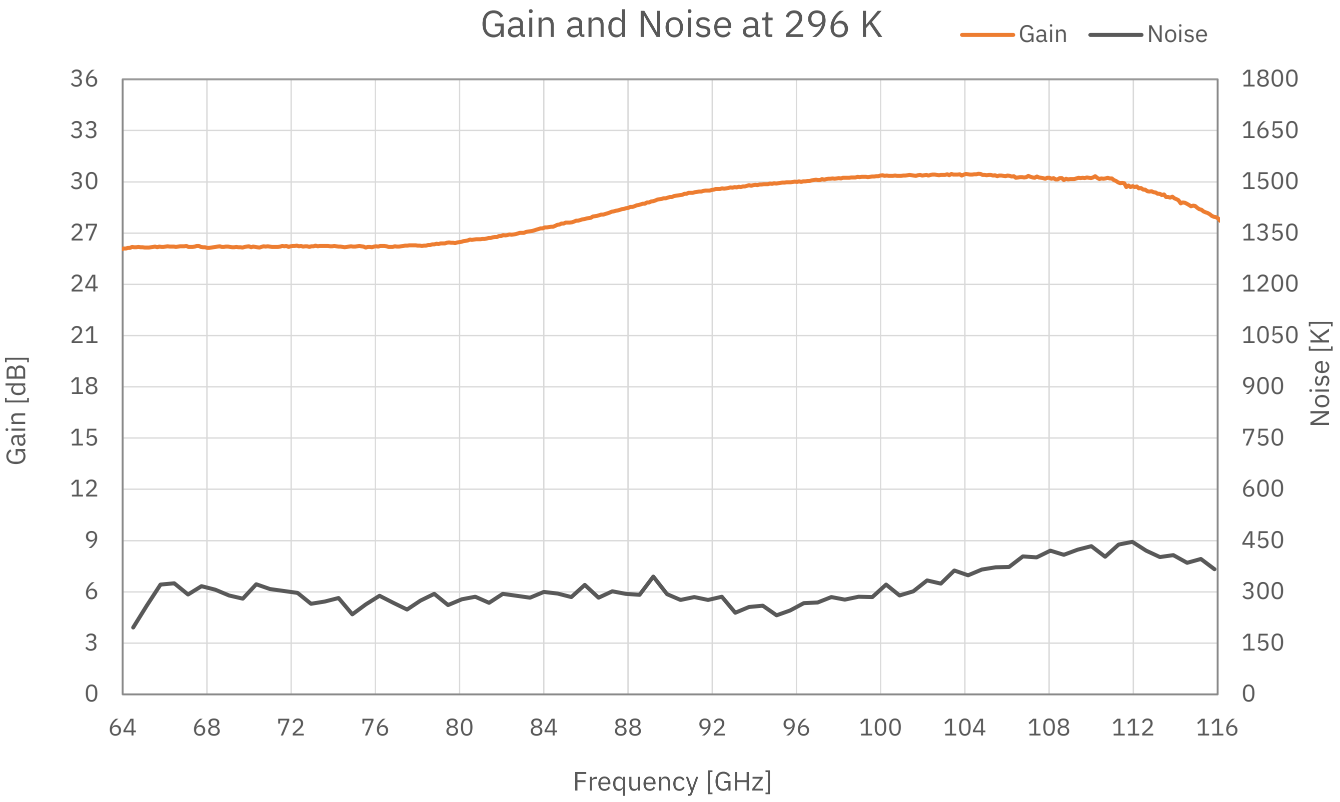
Parameter	Min	Max
DC Voltage on Input and Output	-30 V	30 V
RF Input Power		0 dBm
Operating Temperature	-40 °C	+85 °C

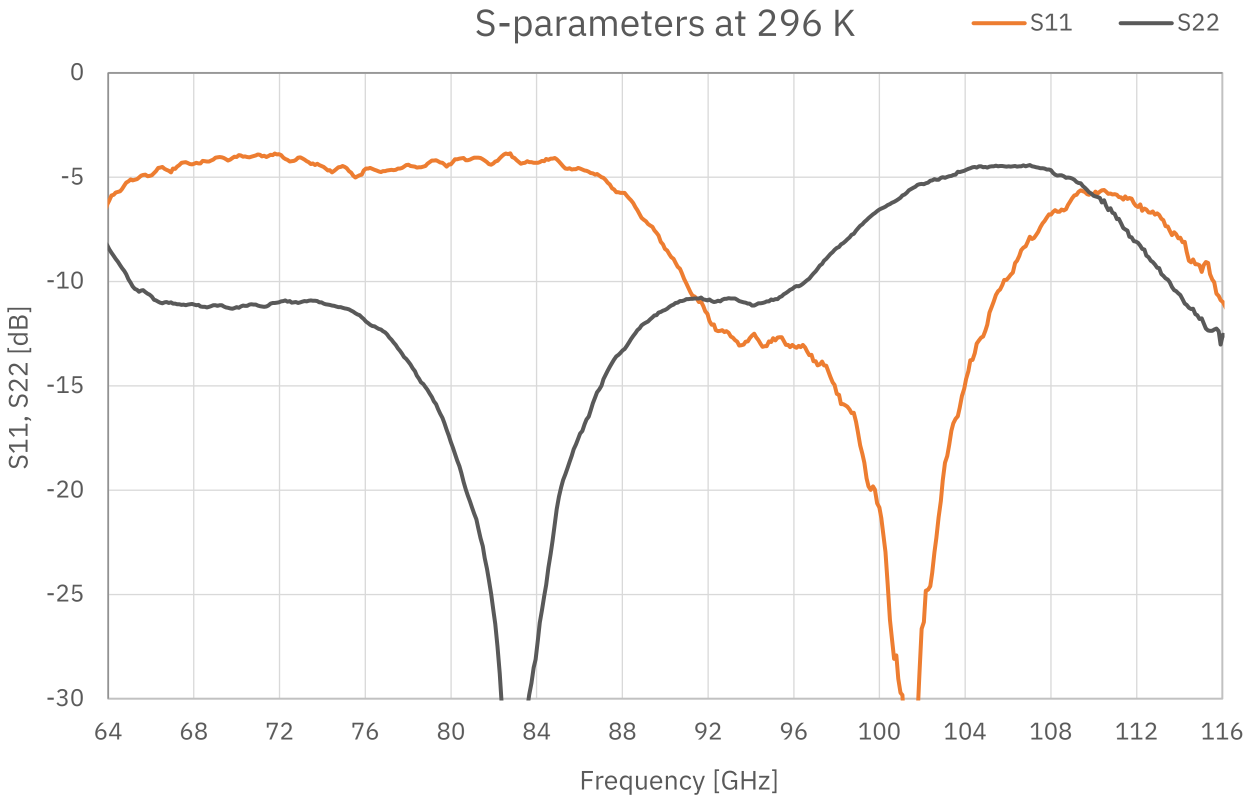
Typical Characteristics

Parameter	Value	Unit
IRL	5	dB
ORL	10	dB
Output P1dB	TBD	dBm
OIP3	TBD	dBm
Weight	16	grams

LNF-LNR65_115WD_SV is a room temperature amplifier using LNF’s proprietary InP HEMT technology. MMIC technology ensures excellent unit-to-unit variation. The LNA is packaged in a waveguide module using industry standard WR10 connectors for the RF ports and 2-pin turret connectors to provide the DC. The lightweight gold plated aluminum body measures 14.92x23.00x19.20 mm excluding the connectors. The LNA is not hermetic and must be operated in a vacuum environment when below the dewpoint. All amplifiers are tested at 296 K and delivered with a test report.

Measured data, T_{amb} = 296 K





Dimensions and wiring

Units: mm